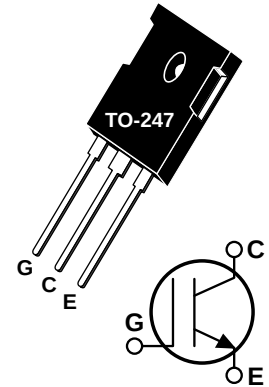


POWER MOS 7® IGBT

A new generation of high voltage power IGBTs. Using punch-through technology and a proprietary metal gate, this IGBT has been optimized for very fast switching, making it ideal for high frequency, high voltage switch-mode power supplies and tail current sensitive applications. In many cases, the POWER MOS 7® IGBT provides a lower cost alternative to a Power MOSFET.

- **Low Conduction Loss**
- **Low Gate Charge**
- **Ultrafast Tail Current shutoff**
- **100 kHz operation @ 400V, 37A**
- **200 kHz operation @ 400V, 24A**
- **SSOA rated**



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT30GP60B	UNIT
V_{CES}	Collector-Emitter Voltage	600	Volts
V_{GE}	Gate-Emitter Voltage	± 20	
V_{GEM}	Gate-Emitter Voltage Transient	± 30	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	100	Amps
I_{C2}	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	49	
I_{CM}	Pulsed Collector Current ^① @ $T_C = 25^\circ\text{C}$	120	
SSOA	Switching Safe Operating Area @ $T_J = 150^\circ\text{C}$	120A @ 600V	
P_D	Total Power Dissipation	463	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{CES}	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 250\mu A$)	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 1mA, T_J = 25^\circ\text{C}$)	3	4.5	6	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 30A, T_J = 25^\circ\text{C}$)		2.2	2.7	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 30A, T_J = 125^\circ\text{C}$)		2.1		
I_{CES}	Collector Cut-off Current ($V_{CE} = 600V, V_{GE} = 0V, T_J = 25^\circ\text{C}$) ^②			250	μA
	Collector Cut-off Current ($V_{CE} = 600V, V_{GE} = 0V, T_J = 125^\circ\text{C}$) ^②			2500	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			± 100	nA

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

APT30GP60B

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		3200		pF
C_{oes}	Output Capacitance			295		
C_{res}	Reverse Transfer Capacitance			20		
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 300V$ $I_C = 30A$		7.5		V
Q_g	Total Gate Charge ^③			90		nC
Q_{ge}	Gate-Emitter Charge			20		
Q_{gc}	Gate-Collector ("Miller") Charge			30		
SSOA	Switching SOA	$T_J = 150^\circ C, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu H, V_{CE} = 600V$	120			A
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC(Peak)} = 400V$ $V_{GE} = 15V$ $I_C = 30A$ $R_G = 5\Omega$ $T_J = +25^\circ C$		13		ns
t_r	Current Rise Time			18		
$t_{d(off)}$	Turn-off Delay Time			55		
t_f	Current Fall Time			46		
E_{on1}	Turn-on Switching Energy ^④			260		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤			335		
E_{off}	Turn-off Switching Energy ^⑥			250	330	
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{CC(Peak)} = 400V$ $V_{GE} = 15V$ $I_C = 30A$ $R_G = 5\Omega$ $T_J = +125^\circ C$		13		ns
t_r	Current Rise Time			18		
$t_{d(off)}$	Turn-off Delay Time			84		
t_f	Current Fall Time			80		
E_{on1}	Turn-on Switching Energy ^④			260		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤			508		
E_{off}	Turn-off Switching Energy ^⑥			518	750	

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.27	$^\circ C/W$
$R_{\theta JC}$	Junction to Case (DIODE)			N/A	
W_T	Package Weight			5.90	gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on-energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. (See Figure 24.)

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

APT Reserves the right to change, without notice, the specifications and information contained herein.

TYPICAL PERFORMANCE CURVES

APT30GP60B

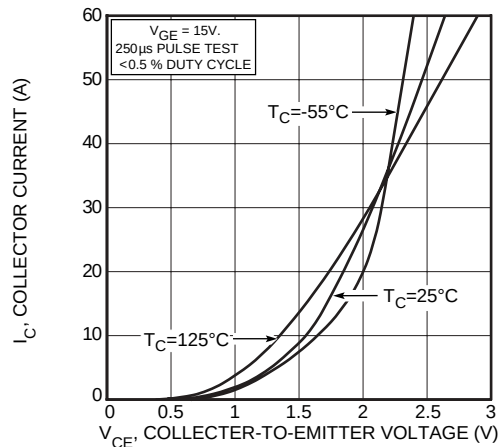


FIGURE 1, Output Characteristics ($V_{GE} = 15V$)

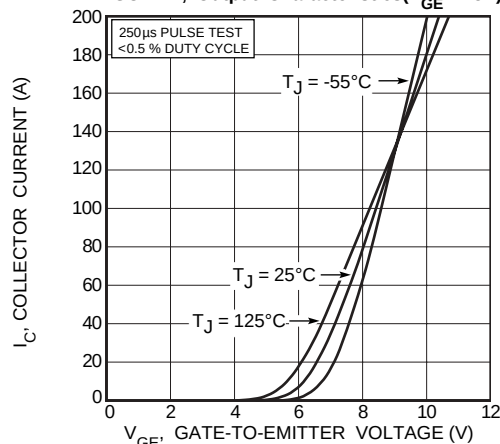


FIGURE 3, Transfer Characteristics

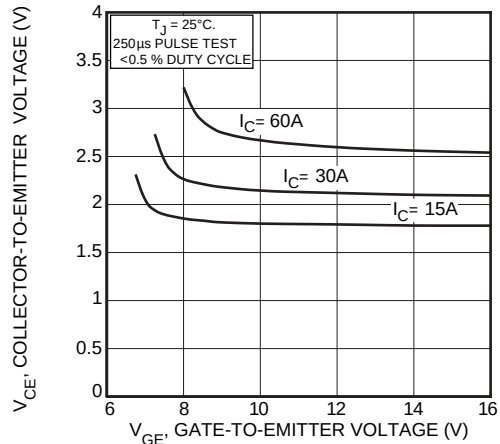


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

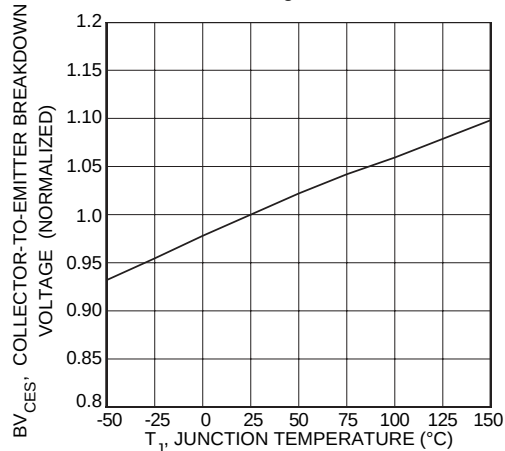


FIGURE 7, Breakdown Voltage vs. Junction Temperature

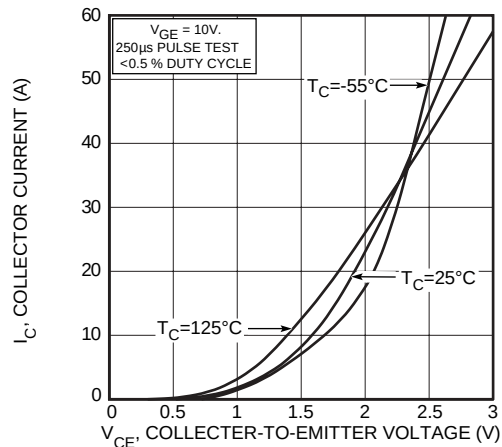


FIGURE 2, Output Characteristics ($V_{GE} = 10V$)

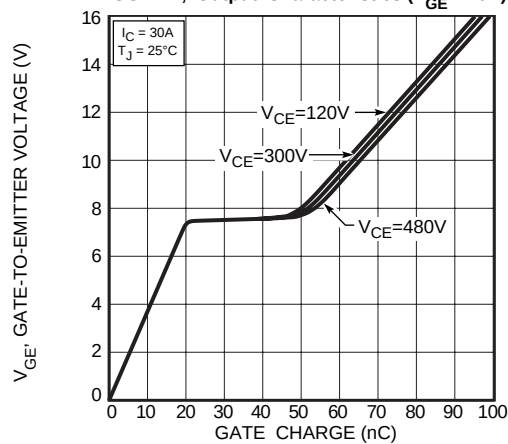


FIGURE 4, Gate Charge

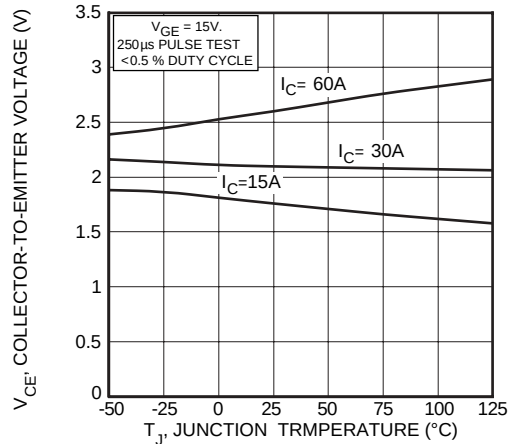


FIGURE 6, On State Voltage vs Junction Temperature

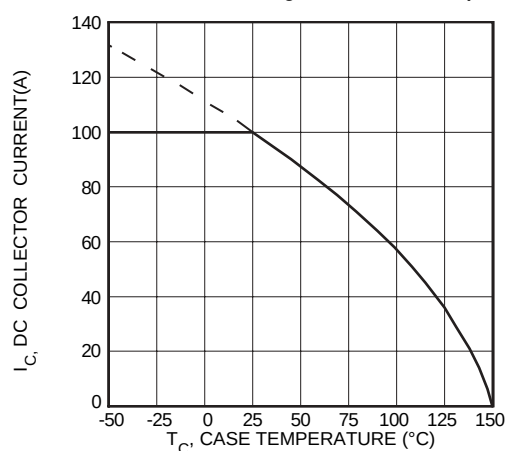


FIGURE 8, DC Collector Current vs Case Temperature

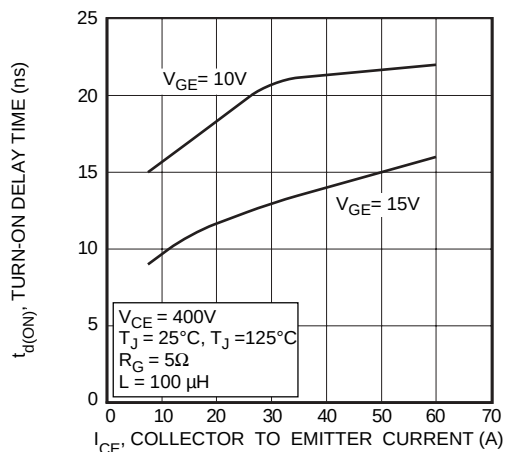


FIGURE 9, Turn-On Delay Time vs Collector Current

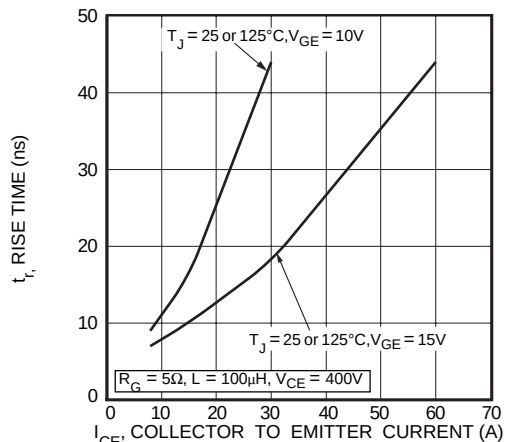


FIGURE 11, Current Rise Time vs Collector Current

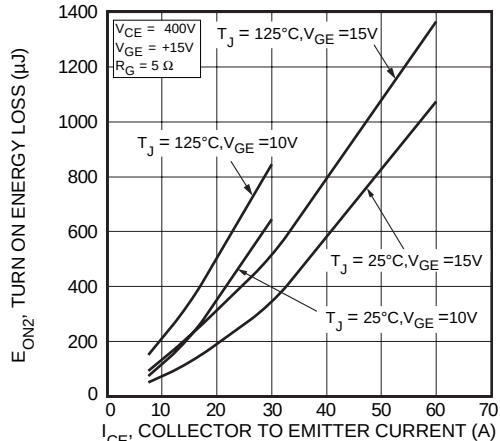


FIGURE 13, Turn-On Energy Loss vs Collector Current

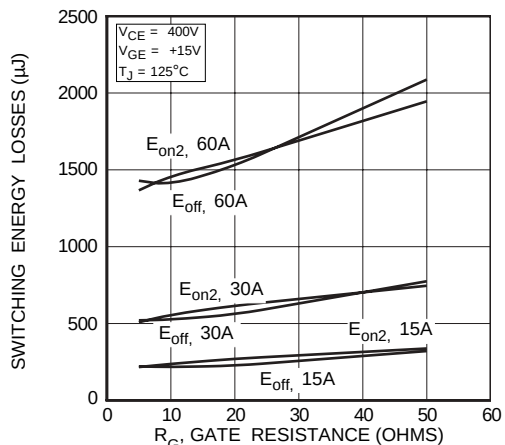


FIGURE 15, Switching Energy Losses vs. Gate Resistance

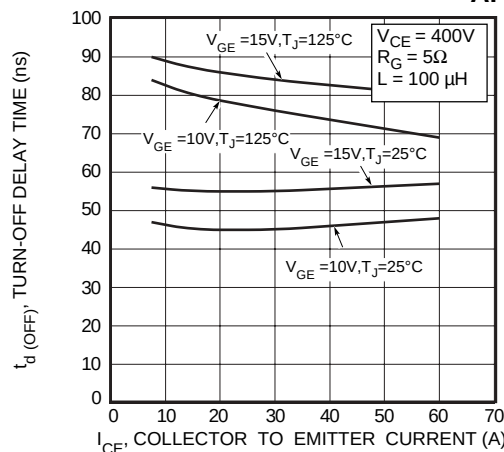


FIGURE 10, Turn-Off Delay Time vs Collector Current

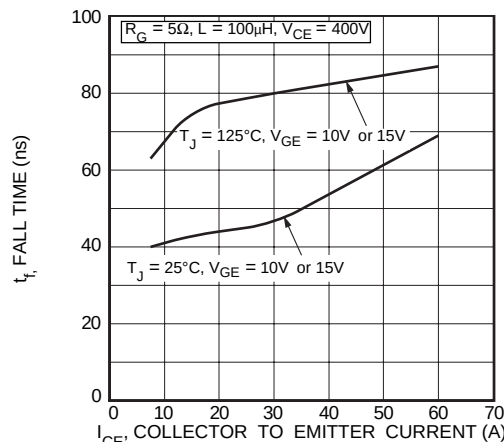


FIGURE 12, Current Fall Time vs Collector Current

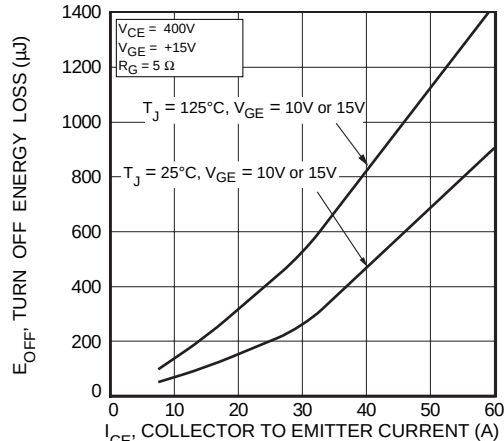


FIGURE 14, Turn Off Energy Loss vs Collector Current

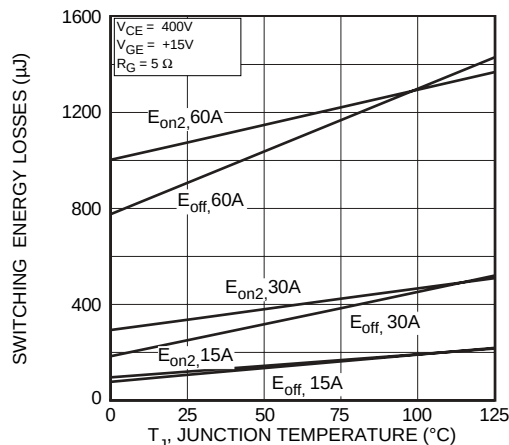


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

APT30GP60B

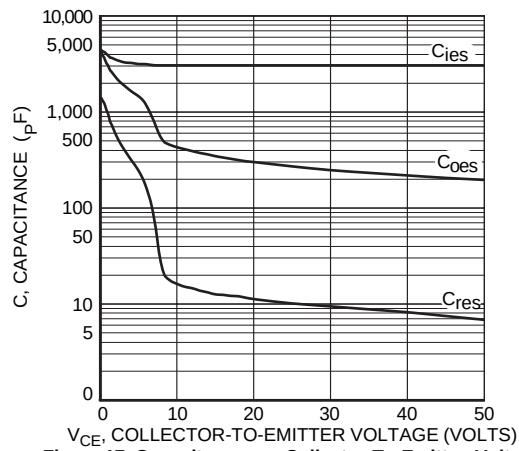


Figure 17, Capacitance vs Collector-To-Emitter Voltage

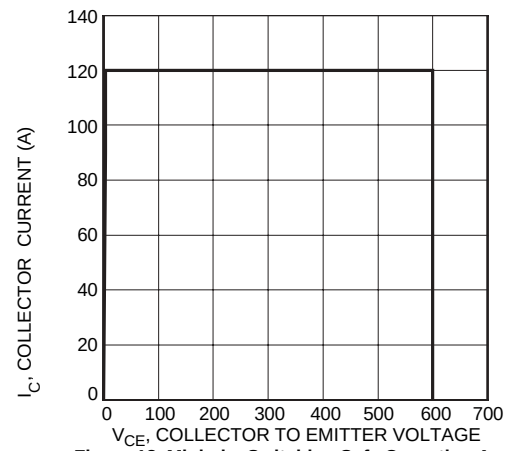


Figure 18, Minimum Switching Safe Operating Area

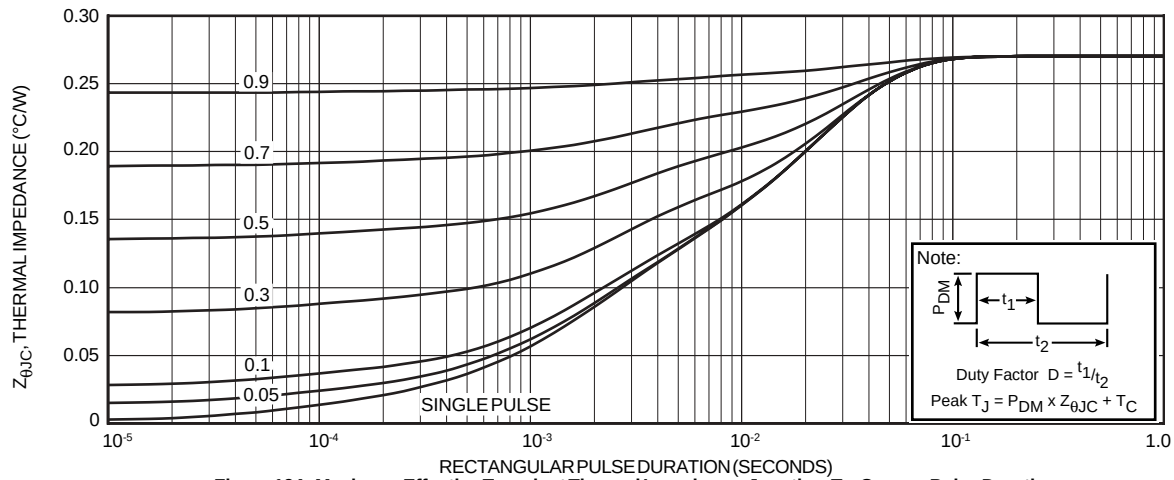


Figure 19A, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

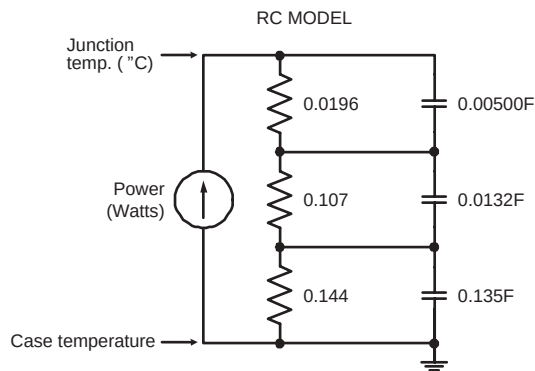


FIGURE 19B, TRANSIENT THERMAL IMPEDANCE MODEL

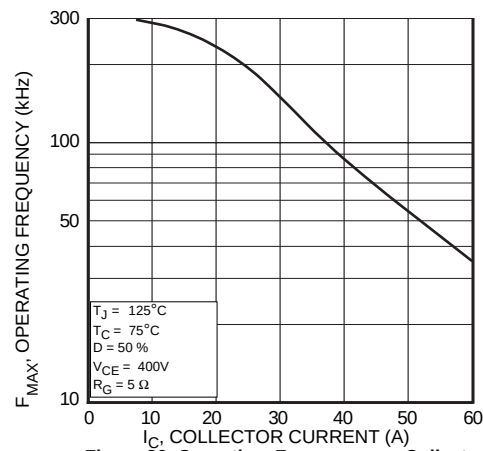


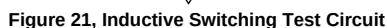
Figure 20, Operating Frequency vs Collector Current

$$F_{\max} = \min(f_{\max 1}, f_{\max 2})$$

$$f_{\max 1} = \frac{0.05}{t_{d(\text{on})} + t_r + t_{d(\text{off})} + t_f}$$

$$f_{\max 2} = \frac{P_{\text{diss}} - P_{\text{cond}}}{E_{\text{on2}} + E_{\text{off}}}$$

$$P_{\text{diss}} = \frac{T_J - T_C}{R_{\theta JC}}$$



Technical drawing of the PCB layout for the 2-Plcs. board. The drawing shows the top and bottom views of the board. The top view is a rectangle with dimensions 15.49 (.610) by 20.80 (.819). The bottom view is a rectangle with dimensions 16.26 (.640) by 21.46 (.845). The board features a central gate area with a diameter of 3.50 (.138) and a central collector area with a diameter of 3.81 (.150). The board is divided into three sections: Gate, Collector, and Emitter. The Gate section has a width of 4.50 (.177) Max. and a height of 6.15 (.242) BSC. The Collector section has a width of 4.69 (.185) and a height of 2.21 (.087). The Emitter section has a width of 1.49 (.059) and a height of 2.59 (.102). The board is labeled '2-Plcs.' and 'Dimensions in Millimeters and (Inches)'.

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.